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(54) Title: METHOD FOR FORMING A FILM ON A SUBSTRATE

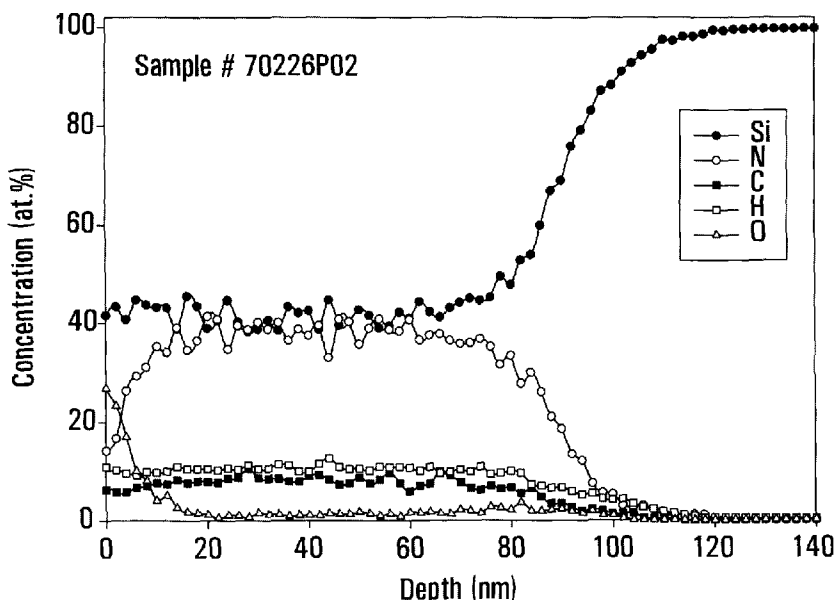


FIG. 1

(57) Abstract: A method for forming a film on a substrate comprising : heating a solid organosilane source in a heating chamber to form a gaseous precursor; transferring the gaseous precursor to a deposition chamber; and reacting the gaseous precursor using an energy source to form the film on the substrate. The film comprises Si and C, and optionally comprises other elements such as N, O, F, B, P, or a combination thereof.

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